

Abstract of the Disclosure:

A MOS transistor in a single-transistor memory cell having a locally thickened gate oxide, and a process for producing the transistor. The MOS transistor can be used as a selection
5 transistor in a single-transistor memory cell having nitride spacers, or another spacer material acting as an oxidation barrier. The transistor also has a bird's beak in the gate oxide to reduce leakage currents. The MOS transistor can be used in a DRAM, particularly as a selection transistor.

MPW/bb